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L Number	Hits	Search Text	DB	Time stamp
1	715	(MRAM (magnetic near3 memory)) and dummy	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/12/22 20:47
2	30	(MRAM (magnetic near3 memory)) and (dummy with (reference adj2 (voltage potential bias)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/12/22 20:48
-	135369	memory and magnetic	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/11 11:43
-	5	(memory and magnetic) and ((first and second) with (magnetic adj3 layer)) and (insulat\$3 near3 film) and (reference near3 voltage) and (dummy near3 cell)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/11 11:52
-	15	(memory and magnetic) and (magnetic adj3 layer) and (insulat\$3 near3 film) and (reference near3 voltage) and (dummy near3 cell)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/11 12:05
-	161	(memory adj2 cell) and (insulat\$3 near3 film) and (magnet\$8 near3 direction) and (magnet\$8 near3 layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/11 12:08
-	161	(memory adj2 cell) and (magnet magnetic) and (insulat\$3 near3 film) and (magnet\$8 near3 direction) and (magnet\$8 near3 layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/11 12:08
-	1730	MRAM	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/24 17:08
-	295	MRAM and (second near3 magnetic near3 layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/24 17:09
-	11	(MRAM and (second near3 magnetic near3 layer)) and (dummy near3 cell)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/24 17:09